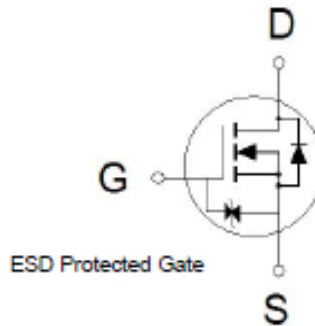
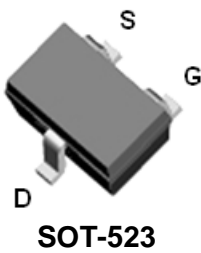


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N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	$3\Omega @ V_{GS} = 4V$	0.3A



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ²	$T_A = 25\text{ }^\circ\text{C}$	I_D	0.3	A
	$T_A = 70\text{ }^\circ\text{C}$		0.2	
Pulsed Drain Current ¹		I_{DM}	3	
Avalanche Current		I_{AS}	1.2	
Avalanche Energy	$L = 1\text{mH}$	E_{AS}	0.8	mJ
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	P_D	0.5	W
	$T_A = 70\text{ }^\circ\text{C}$		0.3	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		220	$^\circ\text{C} / \text{W}$

¹Limited by maximum junction temperature.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 100μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 100μA	0.9	1.3	1.5	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±16V			±30	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 70 °C			10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4V, I _D = 0.1A		1	3	Ω
		V _{GS} = 2.5V, I _D = 0.01A		2	6	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 0.1A		1		S
DYNAMIC						
Input Capacitance	C _{iss (VDS=15V)}	V _{GS} = 0V, f = 1MHz		35		pF
	C _{iss(VDS=5V)}			37		
Output Capacitance	C _{oss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		9		pF
Reverse Transfer Capacitance	C _{riss}			5		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		518		Ω
Turn-On Delay Time ²	t _{d(on)}	V _{DD} = 15V, I _D ≅ 0.1A, V _{GS} = 4V, R _{GEN} = 6Ω		21		nS
Rise Time ²	t _r			45		
Turn-Off Delay Time ²	t _{d(off)}			86		
Fall Time ²	t _f			88		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I _S				0.3	A
Forward Voltage ¹	V _{SD}	I _F = 0.1A, V _{GS} = 0V			1.3	V

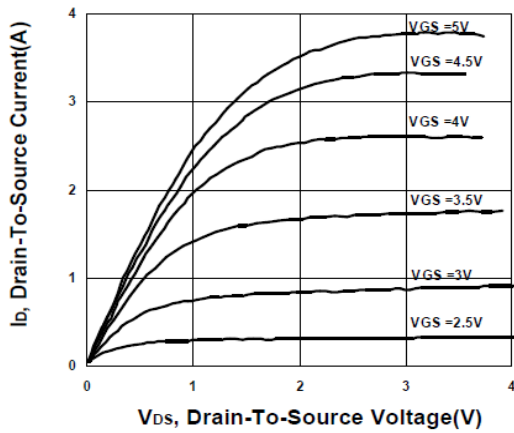
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

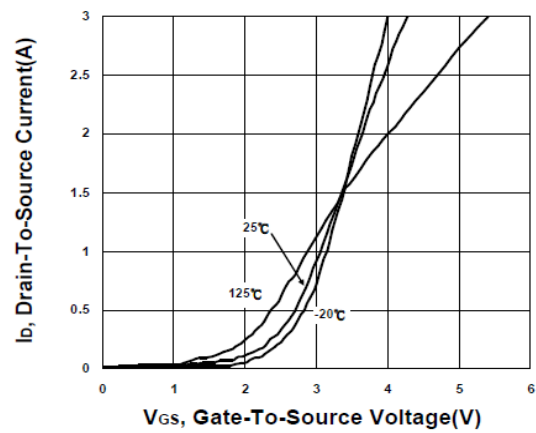
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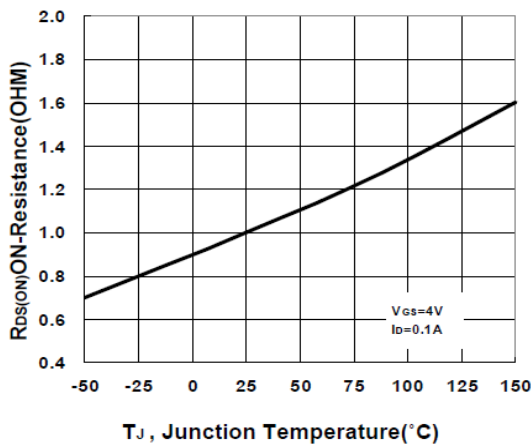
Output Characteristics



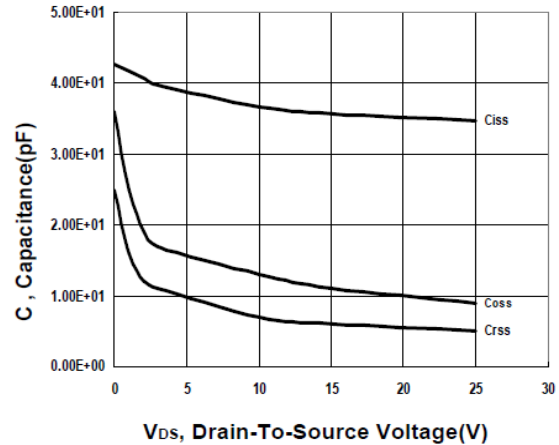
Transfer Characteristics



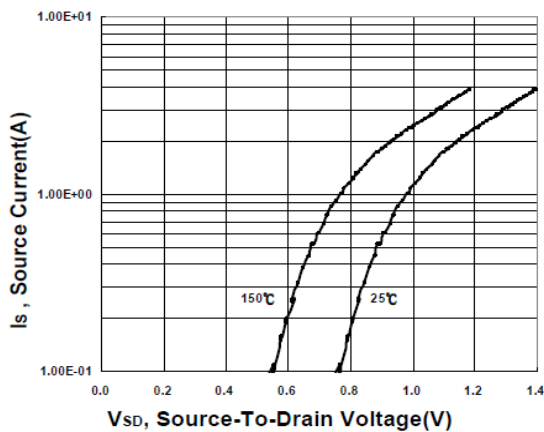
On-Resistance VS Temperature



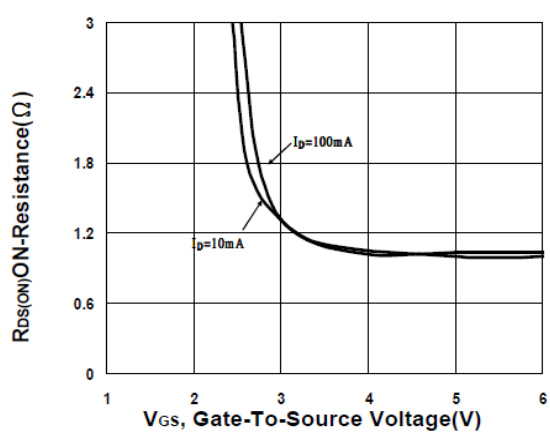
Capacitance Characteristic



Source-Drain Diode Forward Voltage



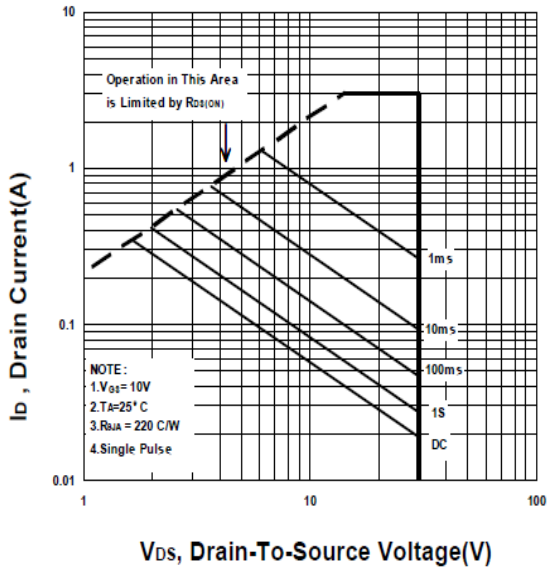
ON-Resistance VS Gate-To-Source Voltage



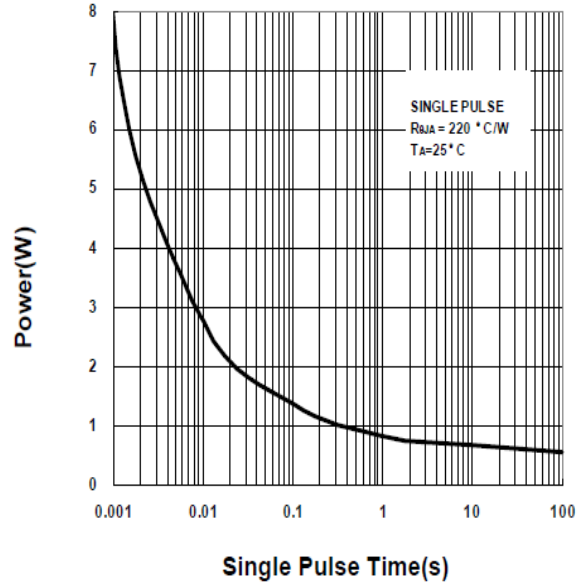
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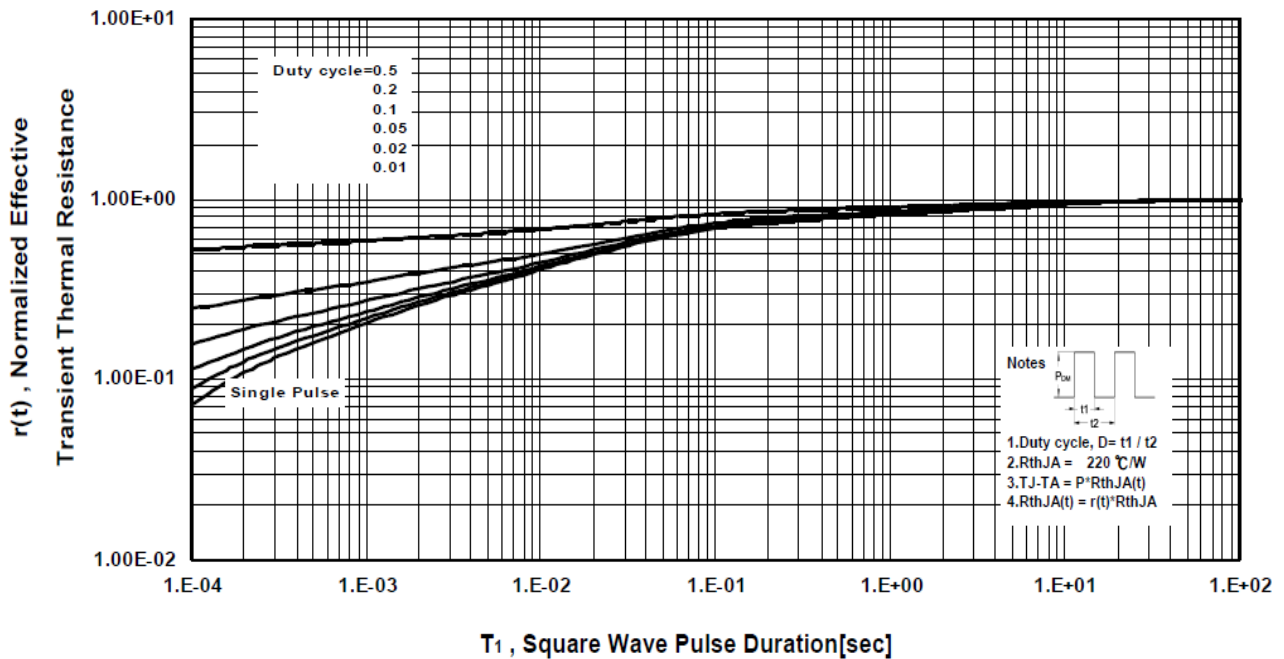
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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Package Dimension

SOT-523 MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	1.5		1.7	H	0.1		0.2
B	0.9		1.1	J	0		0.1
C	0.15		0.25	K	0.7		0.9
D	1.45		1.75	L		0.55	
E	0.25		0.325	M	0.28		0.44
F		0.5		N	0.75		0.85
G	0.7		0.8				

